

DUAL DIGITAL ISOLATOR

Check for Samples: ISO7221C-HT

FEATURES

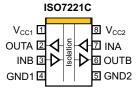
- 1-, 5- and 25-Mbps Signaling Rate Options
 - Low Channel-to-Channel Output Skew;
 1 ns max
 - Low Pulse-Width Distortion (PWD);
 1 ns max
 - Low Jitter Content; 1 ns Typ at 150 Mbps
- 4000-V_{peak} Isolation, 560 V_{peak} V_{IORM}
 - UL 1577 Approved
 - 50-kV/µs Typical Transient Immunity
- Operates with 3.3-V or 5-V Supplies
- 4-kV ESD Protection
- High Electromagnetic Immunity

APPLICATIONS

- Down-Hole Drilling
- High Temperature Environments

SUPPORTS EXTREME TEMPERATURE APPLICATIONS

- Controlled Baseline
- One Assembly and Test Site
- One Fabrication Site
- Available in Extreme (-55°C to 175°C)
 Temperature Range (1) (2)
- Extended Product Life Cycle
- Extended Product-Change Notification
- Product Traceability
- Texas Instruments high temperature products utilize highly optimized silicon (die) solutions with design and process enhancements to maximize performance over extended temperatures.



- (1) Custom temperature ranges available.
- (2) Device is qualified to ensure reliable operation for 1000 hours at maximum rated temperature. This includes, but is not limited to temperature bake, temperature cycle, electro migration, bond inter metallic life, and mold compound life. Such qualification testing should not be viewed as justifying use of this component beyond specified performance and environmental limits.

DESCRIPTION

The ISO7221 is a dual-channel digital isolator. To facilitate PCB layout, the channels are oriented in the opposite directions. This device has a logic input and output buffer separated by Tl's silicon-dioxide (SiO₂) isolation barrier, providing galvanic isolation of up to 4000 V. Used in conjunction with isolated power supplies, this device blocks high voltage, isolates grounds, and prevents noise currents on a data bus or other circuits from entering the local ground and interfering with or damaging sensitive circuitry.

A binary input signal is conditioned, translated to a balanced signal, then differentiated by the capacitive isolation barrier. Across the isolation barrier, a differential comparator receives the logic transition information, then sets or resets a flip-flop and the output circuit accordingly. A periodic update pulse is sent across the barrier to ensure the proper dc level of the output. If this dc-refresh pulse is not received every 4 μ s, the input is assumed to be unpowered or not being actively driven, and the failsafe circuit drives the output to a logic high state.

The small capacitance and resulting time constant provide fast operation with signaling rates available from 0 Mbps (dc) to 150 Mbps. $^{(3)}$ The A-, B- and C-option devices have TTL input thresholds and a noise filter at the input that prevents transient pulses from being passed to the output of the device. The M-option devices have CMOS $V_{\rm CC}/2$ input thresholds and do not have the input noise-filter and the additional propagation delay.

(3) The signaling rate of a line is the number of voltage transitions that are made per second expressed in the units bps (bits per second).

Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet.



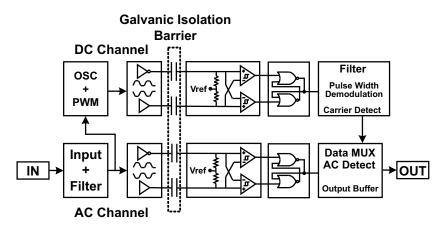
This device requires two supply voltages of 3.3 V, 5 V, or any combination. All inputs are 5-V tolerant when supplied from a 3.3-V supply and all outputs are 4-mA CMOS.

The ISO7221 is characterized for operation over the ambient temperature range of -55°C to 175°C.



These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

SINGLE-CHANNEL FUNCTION DIAGRAM



AVAILABLE OPTIONS(1)

PROD	UCT	MAX SIGNALING RATE	PACKAGE ⁽²⁾	INPUT THRESHOLD	MARKED AS	ORDERING NUMBER
ISO72	221C	25 Mbps	SOIC-8	≉ 1.5 V (TTL) (CMOS compatible)	I7221H	ISO7221CHD

- (1) For the most current package and ordering information, see the Package Option Addendum at the end of this document, or see the TI web site at www.ti.com.
- (2) Package drawings, thermal data, and symbolization are available at www.ti.com/packaging.

REGULATORY INFORMATION

UL
Recognized under 1577 Component Recognition Program ⁽¹⁾
File Number: E181974

 Production tested ≥3000 VRMS for 1 second in accordance with UL 1577.

ABSOLUTE MAXIMUM RATINGS(1)

					VALUE	UNIT
V_{CC}	Supply voltage	⁽²⁾ , V _{CC1} , V _{CC2}			-0.5 to 6	V
V_{I}	V _I Voltage at IN, OUT			-0.5 to 6	V	
Io	lo Output current			±15	mA	
		Human Body Model	Electrostatic discharge JEDEC Standard 22, Test Method A114-C.01		±4	kV
ESD	Electrostatic discharge	Field-Induced-Charged Device Model	JEDEC Standard 22, Test Method C101	All pins	±1	KV
		Machine Model	ANSI/ESDS5.2-1996		±200	V
T_{J}	T _J Maximum junction temperature				180	°C

⁽¹⁾ Stresses beyond those listed under absolute maximum ratings may cause permanent damage to the device. These are stress ratings only and functional operation of the device at these or any other conditions beyond those indicated under recommended operating conditions is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

(2) All voltage values except differential I/O bus voltages are with respect to network ground terminal and are peak voltage values.



RECOMMENDED OPERATING CONDITIONS

		MIN	TYP	MAX	UNIT
V_{CC}	Supply voltage ⁽¹⁾ , V _{CC1} , V _{CC2}	3		5.5	V
I _{OH}	High-level output current			4	mA
I _{OL}	Low-level output current	-4			mA
t _{ui}	Input pulse width ⁽²⁾	40	33		ns
1/t _{ui}	Signaling rate ⁽²⁾	0	30	25	Mbps
V_{IH}	High-level input voltage	2		V_{CC}	V
V_{IL}	Low-level input voltage	0		0.8	V
T _A	Operating temperature	-55		175	°C

 ⁽¹⁾ For the 5-V operation, V_{CC1} or V_{CC2} is specified from 4.5 V to 5.5 V. For the 3-V operation, V_{CC1} or V_{CC2} is specified from 3 V to 3.6 V.
 (2) Typical signaling rate and Input pulse width are measured at ideal conditions at 25°C.

ELECTRICAL CHARACTERISTICS: V_{CC1} and V_{CC2} at 5-V $^{(1)}$ OPERATION

over recommended operating conditions (unless otherwise noted)

	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
SUPPL	Y CURRENT					
I _{CC1}	25 Mbps	V _I = V _{CC} or 0 V, no load		12	22	mA
I _{CC2}	25 Mbps	$V_I = V_{CC}$ or 0 V, no load		12	22	
\/	High lovel output valtage	I _{OH} = -4 mA, See Figure 1	$V_{CC} - 0.8$	4.6		V
V _{OH}	High-level output voltage	$I_{OH} = -20 \mu A$, See Figure 1	V _{CC} - 0.1	5		
.,	Laur laural austraut vielta era	I _{OL} = 4 mA, See Figure 1		0.2	0.4	V
V _{OL}	Low-level output voltage	I _{OL} = 20 μA, See Figure 1		0	0.1	V
$V_{I(HYS)}$	Input voltage hysteresis			150		mV
I _{IH}	High-level input current	IN from 0 V to V _{CC}			11	μΑ
I _{IL}	Low-level input current	IN from 0 V to V _{CC}	-11			μΑ
Cı	Input capacitance to ground	IN at V_{CC} , $V_{I} = 0.4 \sin (4E6\pi t)$		1		pF
CMTI	Common-mode transient immunity	V _I = V _{CC} or 0 V, See Figure 3	25	50		kV/μs

⁽¹⁾ For the 5-V operation, V_{CC1} or V_{CC2} is specified from 4.5 V to 5.5 V. For the 3-V operation, V_{CC1} or V_{CC2} is specified from 3 V to 3.6 V.

SWITCHING CHARACTERISTICS: V_{CC1} and V_{CC2} at 5-V OPERATION

over recommended operating conditions (unless otherwise noted)

	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
t _{pLH} , t _{pHL}	Propagation delay	See Figure 1	21	32	43	ns
PWD	Pulse-width distortion $ t_{pHL} - t_{pLH} ^{(1)}$	See Figure 1		1	2	ns
t _{sk(pp)}	Part-to-part skew (2)				10	ns
t _{sk(o)}	Channel-to-channel output skew (3)			0.2	5	ns
t _r	Output signal rise time	See Figure 1		1		ns
t _f	Output signal fall time	See Figure 1		1		ns
t _{fs}	Failsafe output delay time from input power loss	See Figure 2		3		μs

Also referred to as pulse skew.

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 $t_{sk(pp)}$ is the magnitude of the difference in propagation delay times between any specified terminals of two devices when both devices operate with the same supply voltages, at the same temperature, and have identical packages and test circuits.

t_{sk(o)} is the skew between specified outputs of a single device with all driving inputs connected together and the outputs switching in the same direction while driving identical specified loads.



ELECTRICAL CHARACTERISTICS: V_{CC1} at 5 V, V_{CC2} at 3.3 V⁽¹⁾ OPERATION

over recommended operating conditions (unless otherwise noted)

	PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
SUPPLY	Y CURRENT						
I _{CC1}	25 Mbps		V _I = V _{CC} or 0 V, no load		12	22	mA
I _{CC2}	25 Mbps		V _I = V _{CC} or 0 V, no load		6	12	mA
V_{OH}	Lligh level output valtage	(5-V side)	I _{OH} = -4 mA, See Figure 1	V _{CC} - 0.8			V
	High-level output voltage		I _{OH} = -20 μA, See Figure 1	V _{CC} - 0.1			'
.,	Low lovel output veltoge		I _{OL} = 4 mA, See Figure 1			0.4	V
V _{OL}	Low-level output voltage	Low-level output voltage				0.1	V
$V_{I(HYS)}$	Input voltage hysteresis				150		mV
I _{IH}	High-level input current		IN from 0 V to V _{CC}			11	μΑ
I _{IL}	Low-level input current		IN from 0 V to V _{CC}	-11			μΑ
Cı	Input capacitance to ground		IN at V_{CC} , $V_I = 0.4 \sin (4E6\pi t)$		1		pF
CMTI	Common-mode transient immunity		V _I = V _{CC} or 0 V, See Figure 3	15	40		kV/µs

⁽¹⁾ For the 5-V operation, V_{CC1} or V_{CC2} is specified from 4.5 V to 5.5 V. For the 3-V operation, V_{CC1} or V_{CC2} is specified from 3 V to 3.6 V.

SWITCHING CHARACTERISTICS: V_{CC1} at 5 V, V_{CC2} at 3.3 V OPERATION

over recommended operating conditions (unless otherwise noted)

	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
t_{pLH}, t_{pHL}	Propagation delay		24	36	49	ns
PWD	Pulse-width distortion $ t_{pHL} - t_{pLH} ^{(1)}$			1	2	ns
t _{sk(pp)}	Part-to-part skew (2)				10	ns
t _{sk(o)}	Channel-to-channel output skew (3)			0.2	10	ns
t _r	Output signal rise time	See Figure 1		2		ns
t _f	Output signal fall time	See Figure 1		2		ns
t _{fs}	Failsafe output delay time from input power loss	See Figure 2		3		μs

⁽¹⁾ Also referred to as pulse skew.

ELECTRICAL CHARACTERISTICS: V_{CC1} at 3.3 V, V_{CC2} at 5 V⁽¹⁾ OPERATION

over recommended operating conditions (unless otherwise noted)

	PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
SUPPLY	CURRENT						
I _{CC1}	25 Mbps		V _I = V _{CC} or 0 V, no load		6	12	mA
I _{CC2}	25 Mbps		V _I = V _{CC} or 0 V, no load		12	22	mA
\/	V _{OH} High-level output voltage (3.3-	(3.3-V side)	I _{OH} = -4 mA, See Figure 1	V _{CC} - 0.4			V
VOH			I _{OH} = -20 μA, See Figure 1	V _{CC} - 0.1			V
\ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \	Laurianal autoritus librara		IOL = 4 mA, See Figure 1			0.4	
V _{OL}	Low-level output voltage		IOL = 20 μA, See Figure 1		0	0.1	
$V_{I(HYS)}$	Input threshold voltage hysteresis				150		mV
I _{IH}	High-level input current		IN from 0 V or V _{CC}			11	μA
I _{IL}	Low-level input current		IN from 0 V or V _{CC}	-11			μA
Cı	Input capacitance to ground		IN at V_{CC} , $V_{I} = 0.4 \sin (4E6\pi t)$		1		pF
CMTI	Common-mode transient immunity		V _I = V _{CC} or 0 V, See Figure 3	15	40		kV/μs

⁽¹⁾ For the 5-V operation, V_{CC1} or V_{CC2} is specified from 4.5 V to 5.5 V. For the 3-V operation, V_{CC1} or V_{CC2} is specified from 3 V to 3.6 V.

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⁽²⁾ t_{sk(pp)} is the magnitude of the difference in propagation delay times between any specified terminals of two devices when both devices operate with the same supply voltages, at the same temperature, and have identical packages and test circuits.

⁽³⁾ t_{sk(o)} is the skew between specified outputs of a single device with all driving inputs connected together and the outputs switching in the same direction while driving identical specified loads.



SWITCHING CHARACTERISTICS: V_{CC1} at 3.3 V, V_{CC2} at 5 V OPERTAION

over recommended operating conditions (unless otherwise noted)

	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
t _{pLH} , t _{pHL}	Propagation delay		24	36	49	ns
PWD	Pulse-width distortion $ t_{pHL} - t_{pLH} ^{(1)}$			1	3	ns
t _{sk(pp)}	Part-to-part skew (2)				10	ns
t _{sk(o)}	Channel-to-channel output skew (3)			0.2	10	ns
t _r	Output signal rise time	See Figure 4		1		
t _f	Output signal fall time	See Figure 1		1		
t _{fs}	Failsafe output delay time from input power loss	See Figure 2		3		μs

⁽¹⁾ Also referred to as pulse skew.

ELECTRICAL CHARACTERISTICS: V_{CC1} and V_{CC2} at 3.3 V⁽¹⁾ OPERATION

over recommended operating conditions (unless otherwise noted)

	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
SUPPL	Y CURRENT				,	
I _{CC1}	25 Mbps	V _I = V _{CC} or 0 V, no load		6	12	mA
I _{CC2}	25 Mbps	V _I = V _{CC} or 0 V, no load		6	12	mA
\/	High-level output voltage	I _{OH} = -4 mA, See Figure 1	V _{CC} - 0.4	3		V
V _{OH}	nigh-level output voltage	$I_{OH} = -20 \mu A$, See Figure 1	V _{CC} - 0.1	3.3		V
\/	Low lovel output valtege	I _{OL} = 4 mA, See Figure 1		0.2	0.4	V
V _{OL}	Low-level output voltage	I _{OL} = 20 μA, See Figure 1		0	0.1	٧
V _{I(HYS)}	Input voltage hysteresis			150		mV
I _{IH}	High-level input current	IN from 0 V or V _{CC}			11	μΑ
I _{IL}	Low-level input current	IN from 0 V or V _{CC}	-11			
Cı	Input capacitance to ground	IN at V_{CC} , $V_{I} = 0.4 \sin (4E6\pi t)$		1		pF
CMTI	Common-mode transient immunity	V _I = V _{CC} or 0 V, See Figure 3	15	40		kV/μs

⁽¹⁾ For the 5-V operation, V_{CC1} or V_{CC2} is specified from 4.5 V to 5.5 V. For the 3-V operation, V_{CC1} or V_{CC2} is specified from 3 V to 3.6 V.

SWITCHING CHARACTERISTICS: V_{CC1} and V_{CC2} at 3.3 V

over recommended operating conditions (unless otherwise noted)

	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
t_{pLH} , t_{pHL}	Propagation delay		25	40	53	ns
PWD	Pulse-width distortion $ t_{pHL} - t_{pLH} ^{(1)}$			1	3	ns
t _{sk(pp)}	Part-to-part skew ⁽²⁾				10	ns
t _{sk(o)}	Channel-to-channel output skew (3)			0.2	5	ns
t _r	Output signal rise time	See Figure 1		2		ns
t _f	Output signal fall time	See Figure 1		2		ns
t _{fs}	Failsafe output delay time from input power loss	See Figure 2		3		μs

⁽¹⁾ Also referred to as pulse skew.

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⁽²⁾ t_{sk(pp)} is the magnitude of the difference in propagation delay times between any specified terminals of two devices when both devices operate with the same supply voltages, at the same temperature, and have identical packages and test circuits.

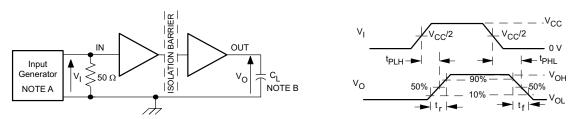
⁽³⁾ t_{sk(o)} is the skew between specified outputs of a single device with all driving inputs connected together and the outputs switching in the same direction while driving identical specified loads.

⁽²⁾ t_{sk(pp)} is the magnitude of the difference in propagation delay times between any specified terminals of two devices when both devices operate with the same supply voltages, at the same temperature, and have identical packages and test circuits.

⁽³⁾ t_{sk(o)} is the skew between specified outputs of a single device with all driving inputs connected together and the outputs switching in the same direction while driving identical specified loads.

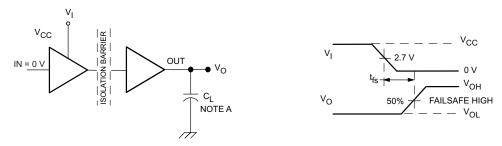


PARAMETER MEASUREMENT INFORMATION



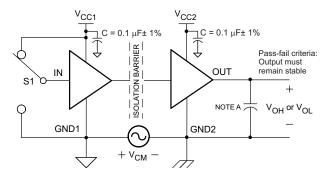
- A. The input pulse is supplied by a generator having the following characteristics: PRR \leq 50 kHz, 50% duty cycle, $t_r \leq$ 3 ns, $t_f \leq$ 3 n
- B. $C_L = 15$ pF and includes instrumentation and fixture capacitance within $\pm 20\%$.

Figure 1. Switching Characteristic Test Circuit and Voltage Waveforms



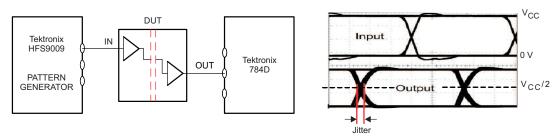
A. $C_L = 15$ pF and includes instrumentation and fixture capacitance within $\pm 20\%$.

Figure 2. Failsafe Delay Time Test Circuit and Voltage Waveforms



A. $C_L = 15 \text{ pF}$ and includes instrumentation and fixture capacitance within $\pm 20\%$.

Figure 3. Common-Mode Transient Immunity Test Circuit



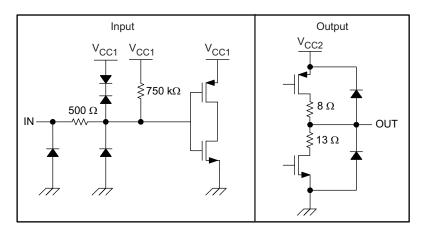
NOTE: PRBS bit pattern run length is $2^{16} - 1$. Transition time is 800 ps.

Figure 4. Peak-to-Peak Eye-Pattern Jitter Test Circuit and Voltage Waveform



DEVICE INFORMATION

DEVICE I/O SCHEMATICS



SOIC-8 PACKAGE THERMAL CHARACTERISTICS

over recommended operating conditions (unless otherwise noted)

	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
θ_{JA}	Junction-to-air	Low-K Thermal Resistance ⁽¹⁾	212			
		High-K Thermal Resistance	122			0000
θ_{JB}	Junction-to-Board Thermal Resistance			37		°C/W
θ_{JC}	Junction-to-Case Thermal Resistance			69.1		•

⁽¹⁾ Tested in accordance with the Low-K or High-K thermal metric definitions of EIA/JESD51-3 for leaded surface mount packages.

DEVICE FUNCTION TABLE

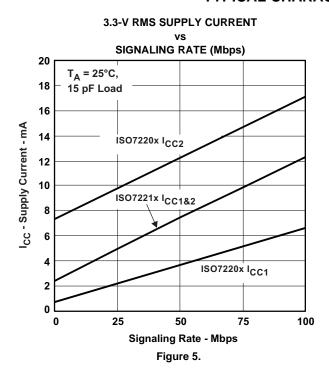
Table 1. Function Table⁽¹⁾

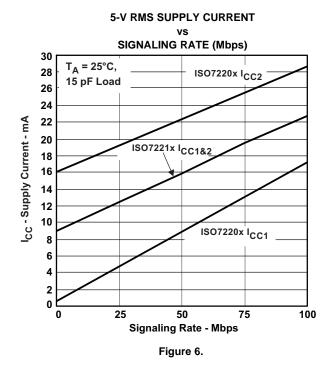
INPUT SIDE V _{CC}	OUTPUT SIDE V _{CC}	INPUT IN	OUTPUT OUT		
		Н	Н		
PU	PU	L	L		
		Open	Н		
PD	PU	Х	Н		

(1) PU = Powered Up(Vcc \geq 3.0V); PD = Powered Down (Vcc \leq 2.5V); X = Irrelevant; H = High Level; L = Low Level

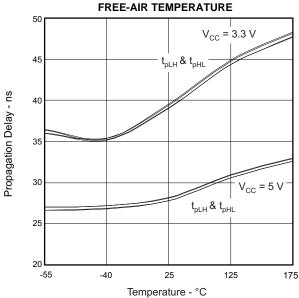


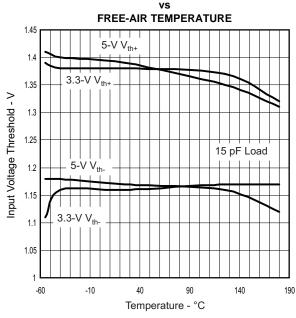
TYPICAL CHARACTERISTIC CURVES





PROPAGATION DELAY vs FREE-AIR TEMPERATURE





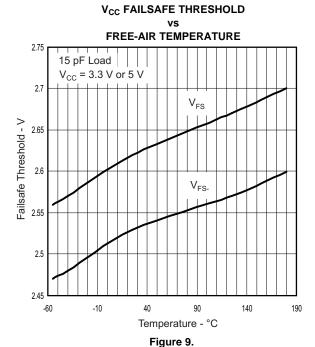
INPUT VOLTAGE LOW-TO-HIGH SWITCHING THRESHOLD

Figure 7.

Figure 8.



TYPICAL CHARACTERISTIC CURVES (continued)

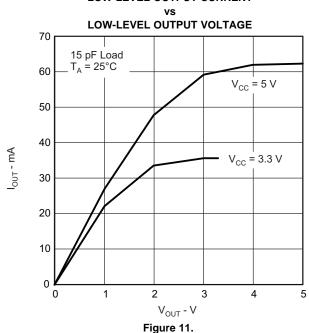


HIGH-LEVEL OUTPUT CURRENT

Figure 10.

 V_{OUT} - V

LOW-LEVEL OUTPUT CURRENT





APPLICATION INFORMATION

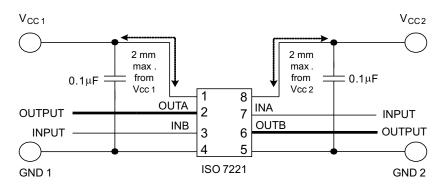
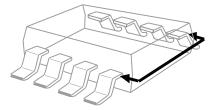


Figure 12. Typical ISO7221 Application Circuit

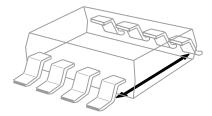


ISOLATION GLOSSARY

Creepage Distance — The shortest path between two conductive input to output leads measured along the surface of the insulation. The shortest distance path is found around the end of the package body.



Clearance — The shortest distance between two conductive input to output leads measured through air (line of sight).



Input-to Output Barrier Capacitance — The total capacitance between all input terminals connected together, and all output terminals connected together.

Input-to Output Barrier Resistance — The total resistance between all input terminals connected together, and all output terminals connected together.

Primary Circuit — An internal circuit directly connected to an external supply mains or other equivalent source which supplies the primary circuit electric power.

Secondary Circuit — A circuit with no direct connection to primary power, and derives its power from a separate isolated source.

Comparative Tracking Index (CTI) — CTI is an index used for electrical insulating materials which is defined as the numerical value of the voltage which causes failure by tracking during standard testing. Tracking is the process that produces a partially conducting path of localized deterioration on or through the surface of an insulating material as a result of the action of electric discharges on or close to an insulation surface -- the higher CTI value of the insulating material, the smaller the minimum creepage distance.

Generally, insulation breakdown occurs either through the material, over its surface, or both. Surface failure may arise from flashover or from the progressive degradation of the insulation surface by small localized sparks. Such sparks are the result of the breaking of a surface film of conducting contaminant on the insulation. The resulting break in the leakage current produces an overvoltage at the site of the discontinuity, and an electric spark is generated. These sparks often cause carbonization on insulation material and lead to a carbon track between points of different potential. This process is known as *tracking*.

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Insulation:

Operational insulation — Insulation needed for the correct operation of the equipment.

Basic insulation — Insulation to provide basic protection against electric shock.

Supplementary insulation — Independent insulation applied in addition to basic insulation in order to ensure protection against electric shock in the event of a failure of the basic insulation.

Double insulation — Insulation comprising both basic and supplementary insulation.

Reinforced insulation — A single insulation system which provides a degree of protection against electric shock equivalent to double insulation.

Pollution Degree:

Pollution Degree 1 — No pollution, or only dry, nonconductive pollution occurs. The pollution has no influence.

Pollution Degree 2 — Normally, only nonconductive pollution occurs. However, a temporary conductivity caused by condensation must be expected.

Pollution Degree 3 — Conductive pollution occurs or dry nonconductive pollution occurs which becomes conductive due to condensation which is to be expected.

Pollution Degree 4 - Continuous conductivity occurs due to conductive dust, rain, or other wet conditions.

Installation Category:

Overvoltage Category — This section is directed at insulation co-ordination by identifying the transient overvoltages which may occur, and by assigning 4 different levels as indicated in IEC 60664.

- I: Signal Level Special equipment or parts of equipment.
- II: Local Level Portable equipment etc.
- III: Distribution Level Fixed installation
- IV: Primary Supply Level Overhead lines, cable systems

Each category should be subject to smaller transients than the category above.

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2-Oct-2012

PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan ⁽²⁾	Lead/ Ball Finish	MSL Peak Temp ⁽³⁾	Samples (Requires Login)
ISO7221CHD	ACTIVE	SOIC	D	8	75	TBD	Call TI	Call TI	

(1) The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

(2) Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check http://www.ti.com/productcontent for the latest availability information and additional product content details.

TBD: The Pb-Free/Green conversion plan has not been defined.

Pb-Free (RoHS): TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes.

Pb-Free (RoHS Exempt): This component has a RoHS exemption for either 1) lead-based flip-chip solder bumps used between the die and package, or 2) lead-based die adhesive used between the die and leadframe. The component is otherwise considered Pb-Free (RoHS compatible) as defined above.

Green (RoHS & no Sb/Br): TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)

(3) MSL, Peak Temp. -- The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

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OTHER QUALIFIED VERSIONS OF ISO7221C-HT:

Catalog: ISO7221C

Automotive: ISO7221C-Q1

NOTE: Qualified Version Definitions:





2-Oct-2012

- Catalog TI's standard catalog product
- Automotive Q100 devices qualified for high-reliability automotive applications targeting zero defects

D (R-PDSO-G8)

PLASTIC SMALL OUTLINE



NOTES:

- A. All linear dimensions are in inches (millimeters).
- B. This drawing is subject to change without notice.
- Body length does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.006 (0,15) each side.
- Body width does not include interlead flash. Interlead flash shall not exceed 0.017 (0,43) each side.
- E. Reference JEDEC MS-012 variation AA.



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